
2SC4807

Silicon NPN Epitaxial

HITACHI

Application

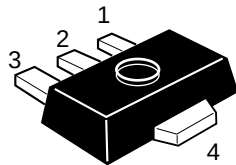
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 $f_T = 4.4 \text{ GHz Typ}$
- High output power
1 dB Power compression point $P_{cp} = 24 \text{ dBm Typ}$ at $V_{CE} = 5V$, $I_C = 100 \text{ mA}$, $f = 900 \text{ MHz}$

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	200	mA
Collector power dissipation	P_C^{*1}	800	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

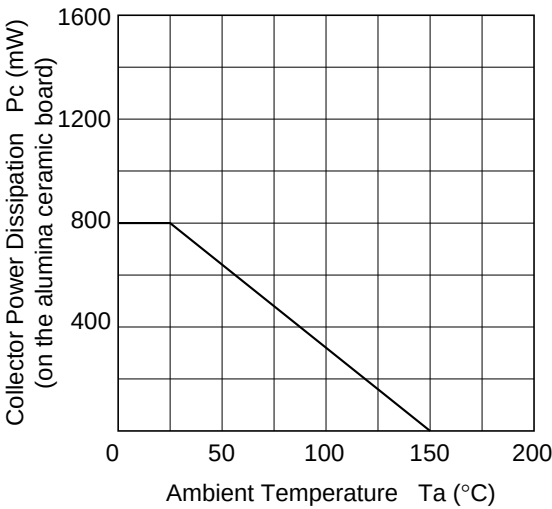
Note: 1. Value on the alumina ceramics board (12.5 x 20 x 0.7 mm)

Electrical Characteristics (Ta = 25°C)

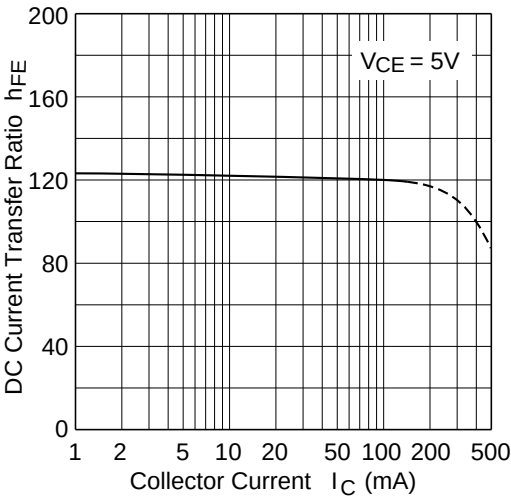
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	30	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 15\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 15\text{ V}$, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 2\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	50	120	250		$V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$
Collector output capacitance	C_{ob}	—	2.8	4.0	pF	$V_{CB} = 5\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$
Gain bandwidth product	f_T	3.0	4.4	—	GHz	$V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$
Power gain	PG	5.0	7.0	—	dB	$V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$, $f = 900\text{ MHz}$
Noise figure	NF	—	2.5	4.0	dB	$V_{CE} = 5\text{ V}$, $I_C = 20\text{ mA}$, $f = 900\text{ MHz}$

Note: Marking is “ER”.

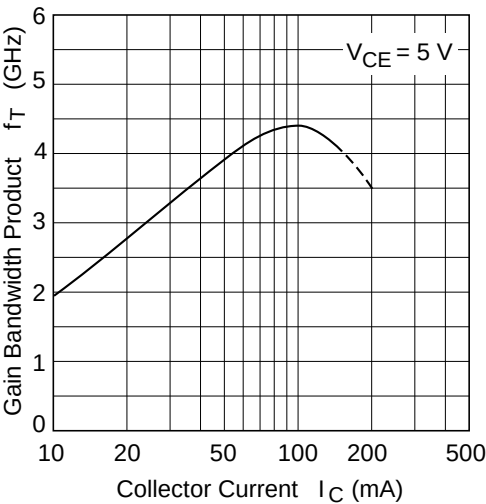
Maximum Collector Dissipation Curve



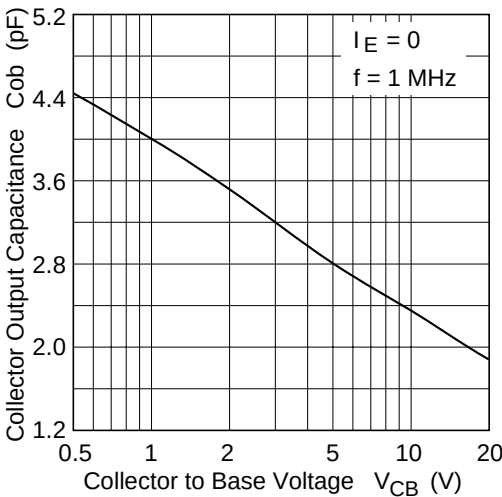
DC Current Transfer Ratio vs. Collector Current



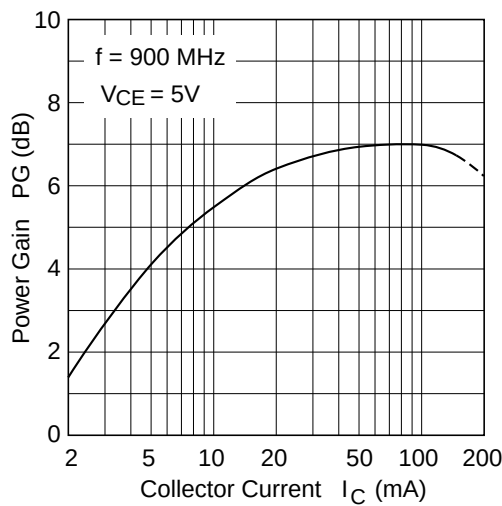
Gain Bandwidth Product vs. Collector Current



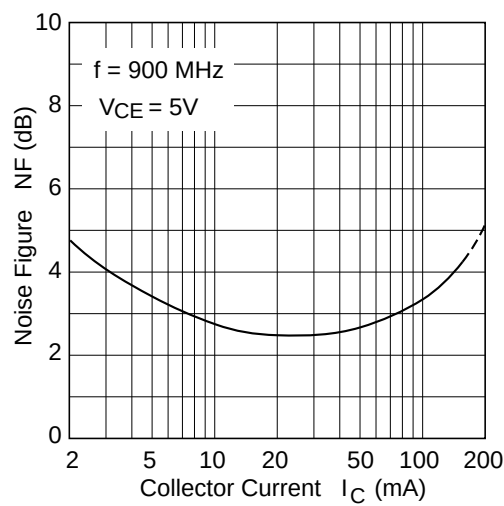
Collector Output Capacitance vs. Collector to Base Voltage



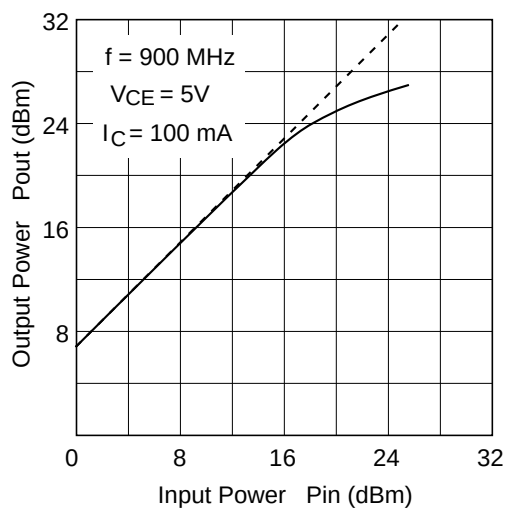
Power Gain vs. Collector Current



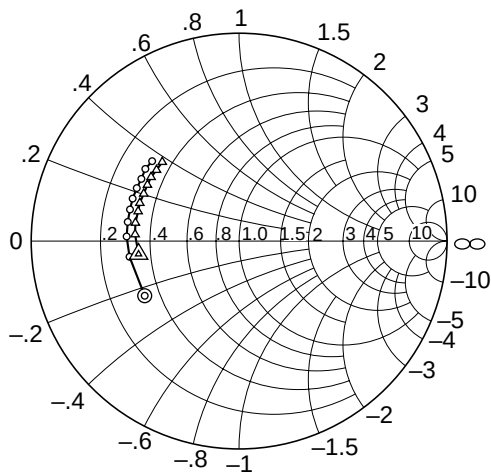
Noise Figure vs. Collector Current



Output Power vs. Input Power

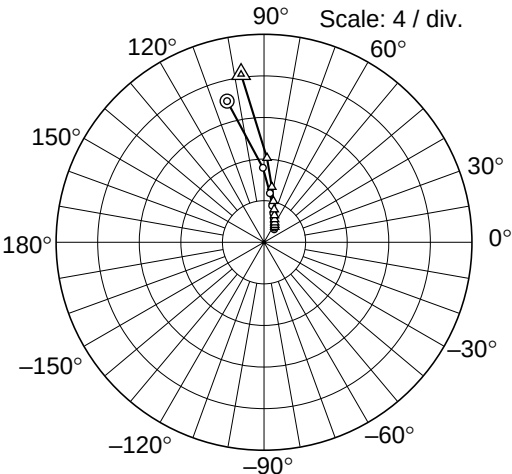


S11 Parameter vs. Frequency



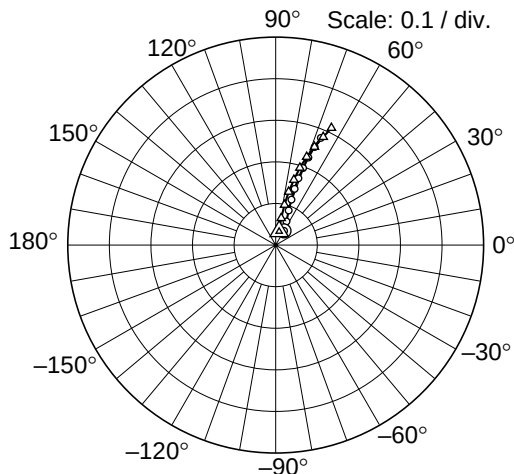
Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
100 to 1000 MHz (100 MHz step)
○ — ○ ($I_C = 20\text{ mA}$)
△ — △ ($I_C = 100\text{ mA}$)

S21 Parameter vs. Frequency



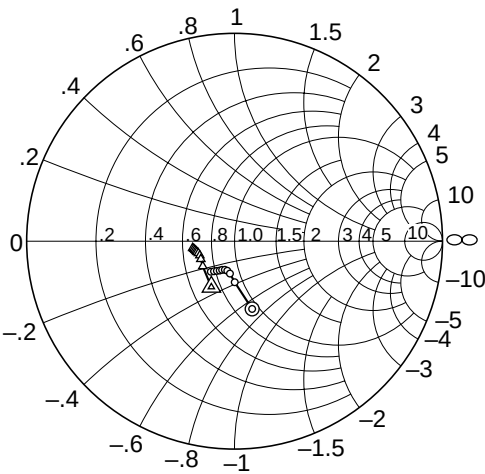
Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
100 to 1000 MHz (100 MHz step)
○ — ○ ($I_C = 20\text{ mA}$)
△ — △ ($I_C = 100\text{ mA}$)

S12 Parameter vs. Frequency



Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
100 to 1000 MHz (100 MHz step)
○ — ○ ($I_C = 20\text{ mA}$)
△ — △ ($I_C = 100\text{ mA}$)

S22 Parameter vs. Frequency



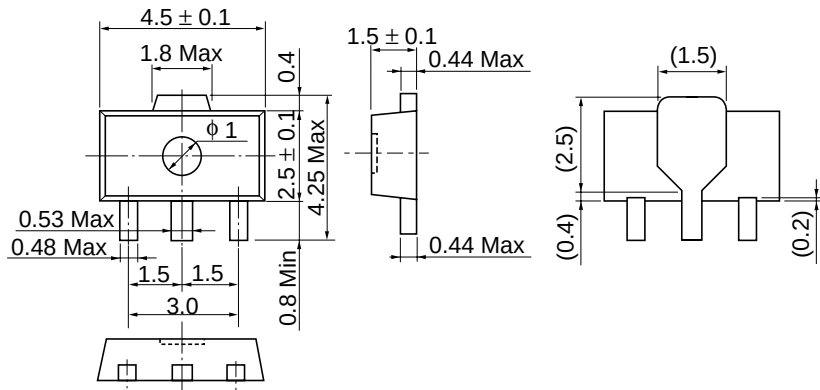
Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
100 to 1000 MHz (100 MHz step)
○ — ○ ($I_C = 20\text{ mA}$)
△ — △ ($I_C = 100\text{ mA}$)

S Parameter (V_{CE} = 5 V, I_C = 20 mA, Z_O = 50 Ω, Emitter Common)

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.525	−150.0	14.03	104.7	0.039	58.4	0.336	−75.5
200	0.533	−171.9	7.16	90.9	0.063	65.7	0.197	−89.9
300	0.542	177.6	4.75	83.2	0.089	69.6	0.157	−98.3
400	0.544	170.2	3.60	77.5	0.116	71.0	0.146	−104.0
500	0.547	163.8	2.91	72.1	0.143	71.5	0.145	−109.0
600	0.552	158.2	2.46	67.4	0.170	71.3	0.150	−113.7
700	0.555	152.6	2.14	63.3	0.197	70.5	0.158	−117.1
800	0.558	147.5	1.90	59.3	0.225	69.6	0.166	−121.0
900	0.570	142.4	1.72	55.2	0.254	68.4	0.175	−124.6
1000	0.569	137.4	1.58	51.9	0.280	67.2	0.186	−128.1

S Parameter (V_{CE} = 5 V, I_C = 100 mA, Z_O = 50 Ω, Emitter Common)

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.488	−172.8	16.32	97.8	0.034	76.2	0.248	−116.9
200	0.502	176.3	8.08	88.0	0.066	78.6	0.195	−141.9
300	0.507	170.0	5.34	82.0	0.099	77.8	0.184	−152.2
400	0.507	163.6	4.03	77.2	0.132	76.4	0.181	−157.9
500	0.514	159.0	3.27	72.8	0.163	74.5	0.184	−161.8
600	0.513	153.6	2.75	68.8	0.195	72.7	0.189	−164.0
700	0.518	148.5	2.40	65.1	0.225	70.7	0.192	−165.8
800	0.524	144.0	2.13	61.3	0.254	68.5	0.196	−167.6
900	0.525	139.3	1.93	57.8	0.284	66.3	0.200	−169.4
1000	0.531	134.2	1.77	54.6	0.312	64.6	0.205	−170.8



Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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